

Features

Field Stop Trench gate IGBT、Low Collector-Emitter saturation voltage、High short circuit capability
Low switching losses

Version

Low Vcesat

Application

Industrial Motor Drivers, Inverter, Welding, UPS

Status

Mass production

Specifications

Gate-Emitter voltage VCES [V]	Collector current IC [A]	Collector- Emitter saturation voltage VCE(sat) @Tj=25deg C typical limit	Collector- Emitter saturation voltage VCE(sat) @Tj=25deg C upper limit	Gate Voltage VGES [V]	Gate-Emitter threshold voltage VGE(th) lower limit [V]	Gate-Emitter threshold voltage VGE(th) upper limit [V]
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MMJ65A0A02xx

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		[V]	[V]			
650	100	1.30	1.60	-30~30	5.00	6.80
Die size X [mm]		Die size Y [mm]		Junction temperature Tj [deg.C]		
7.80		7.80		-40~175		